

**EXAMINATION NO. 3 - SOLUTIONS**

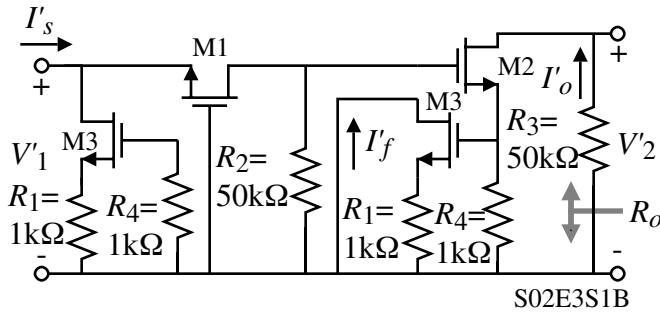
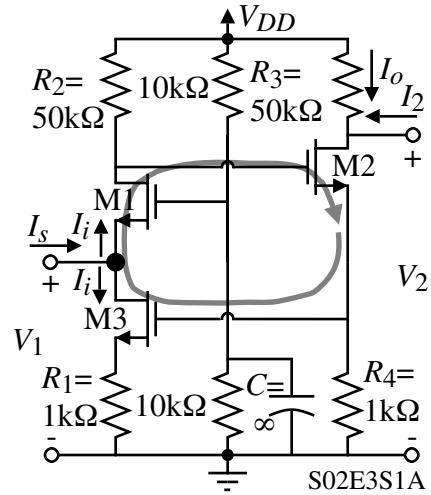
(Average = 47, High = 65, Low = 27)

**Problem 1 - (25 points)**

The simplified schematic of a feedback amplifier is shown. Use the method of feedback analysis to find  $V_2/V_1$ ,  $R_{in} = V_1/I_1$ , and  $R_{out} = V_2/I_2$ . Assume that all transistors are matched and that  $g_m = 1\text{mA/V}$  and  $r_{ds} = \infty$ .

**Solution**

This feedback circuit is shunt-series. We begin with the open-loop, quasi-ac model shown below.



The small-signal, open-loop model is:

$$\frac{I'_o}{I'_s} = \left( \frac{I'_o}{V_{gs2}} \right) \left( \frac{V_{gs2}}{V_{gs1}} \right) \left( \frac{V_{gs1}}{I'_s} \right)$$

$$V_{gs2} = -g_{m1}V_{gs1}R_2 - g_{m2}V_{gs2}R_4$$

or

$$\frac{V_{gs2}}{V_{gs1}} = \frac{-g_{m1}R_2}{1 + g_{m2}R_4} = -\frac{50}{2} = -25 \quad \therefore a = \frac{I'_o}{I'_s} = (g_{m2})(-25)\left(\frac{-1}{g_{m1}}\right) = 25\text{A/A}$$

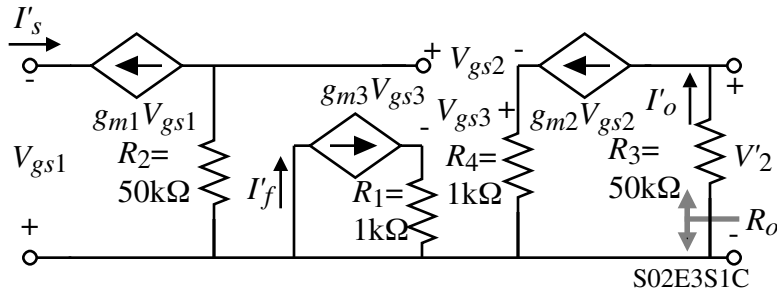
$$f = \frac{I'_f}{I'_o} = \left( \frac{I'_f}{V_{gs3}} \right) \left( \frac{V_{gs3}}{I'_o} \right) = (g_{m3}) \left( \frac{R_4}{1 + g_{m3}R_1} \right) = (1\text{mA/V})(0.5\text{k}\Omega) = 0.5$$

$$\therefore af = 25 \cdot 0.5 = 12.5$$

$$R_i = \frac{v'_1}{I'_s} = \frac{1}{g_{m1}} = 1\text{k}\Omega \rightarrow R_{in} = R_{if} = \frac{R_i}{1 + af} = \frac{1000}{13.5} = 74.07\Omega$$

$$R_{out} = 50\text{k}\Omega \quad (R_3 \text{ is outside the feedback loop})$$

$$\frac{I_o}{I_s} = \frac{a}{1+af} = \frac{25}{1+12.5} = 1.852 \text{ A/A} \rightarrow \frac{v_2}{v_1} = \frac{I_o(-50\text{k}\Omega)}{I_s(74.07\Omega)} = -1240.1 \text{ V/V}$$



**Problem 2 - (25 points)**

Use the Blackman's formula (see below) to calculate the small-signal output resistance of the stacked MOSFET configuration having identical drain-source drops for both transistors. Express your answer in terms of all the pertinent small-signal parameters and then simplify your answer if  $g_m > g_{ds} > (1/R)$ . Assume the MOSFETs are identical.

$$R_{out} = R_{out}(g_m=0) \left[ \frac{1 + RR(\text{output port shorted})}{1 + RR(\text{output port open})} \right]$$

(You may use small-signal analysis if you wish but this circuit seems to be one of the rare cases where feedback analysis is more efficient.)

Solution

$$R_{out}(g_m=0) = 2R \parallel (r_{ds1} + r_{ds2}) = \frac{2R(r_{ds1} + r_{ds2})}{2R + r_{ds1} + r_{ds2}}$$

$RR(\text{port shorted}) = ?$

$$v_r = 0 - v_{s2} = -g_{m2}v_t \left( \frac{r_{ds1}r_{ds2}}{r_{ds1} + r_{ds2}} \right)$$

$$\Rightarrow RR(\text{port shorted}) = \frac{g_{m2}r_{ds1}r_{ds2}}{r_{ds1} + r_{ds2}}$$

$RR(\text{port open}) = ?$

$$v_r = -g_{m2}v_t \left( \frac{r_{ds2}(r_{ds1} + R)}{r_{ds1} + r_{ds2} + 2R} \right)$$

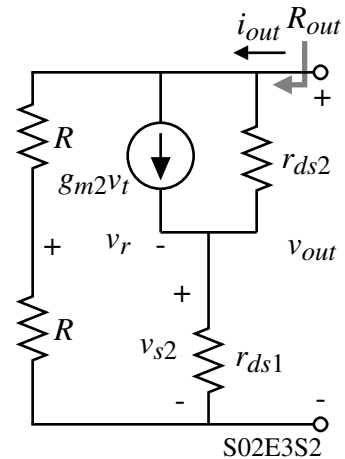
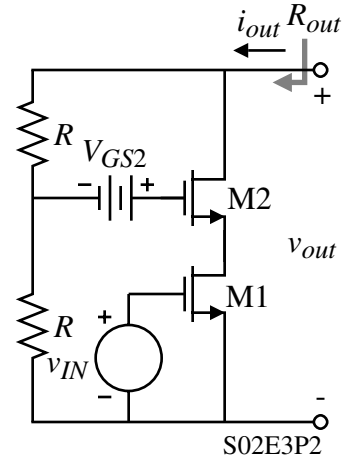
$$\Rightarrow RR(\text{port open}) = \frac{g_{m2}r_{ds2}(r_{ds1} + R)}{r_{ds1} + r_{ds2} + 2R}$$

$$\therefore R_{out} = \frac{2R(r_{ds1} + r_{ds2})}{2R + r_{ds1} + r_{ds2}} \left[ \frac{1 + \frac{g_{m2}r_{ds1}r_{ds2}}{r_{ds1} + r_{ds2}}}{1 + \frac{g_{m2}r_{ds2}(r_{ds1} + R)}{r_{ds1} + r_{ds2} + 2R}} \right] = 2R \left( \frac{r_{ds1} + r_{ds2} + g_{m2}r_{ds1}r_{ds2}}{r_{ds1} + r_{ds2} + 2R + g_{m2}r_{ds2}(r_{ds1} + R)} \right)$$

Using the assumptions of  $g_m > g_{ds} > (1/R)$  we can simplify  $R_{out}$  as

$$R_{out} \approx 2R \left( \frac{g_{m2}r_{ds1}r_{ds2}}{g_{m2}r_{ds2}R} \right) = \underline{\underline{2r_{ds1}}}$$

What is the insight? Well there are two feedback loops, one a series (the normal cascode) and one a shunt. Apparently they are working against each other and the effective output resistance is pretty much what it would be if there were two transistors in series without any feedback.

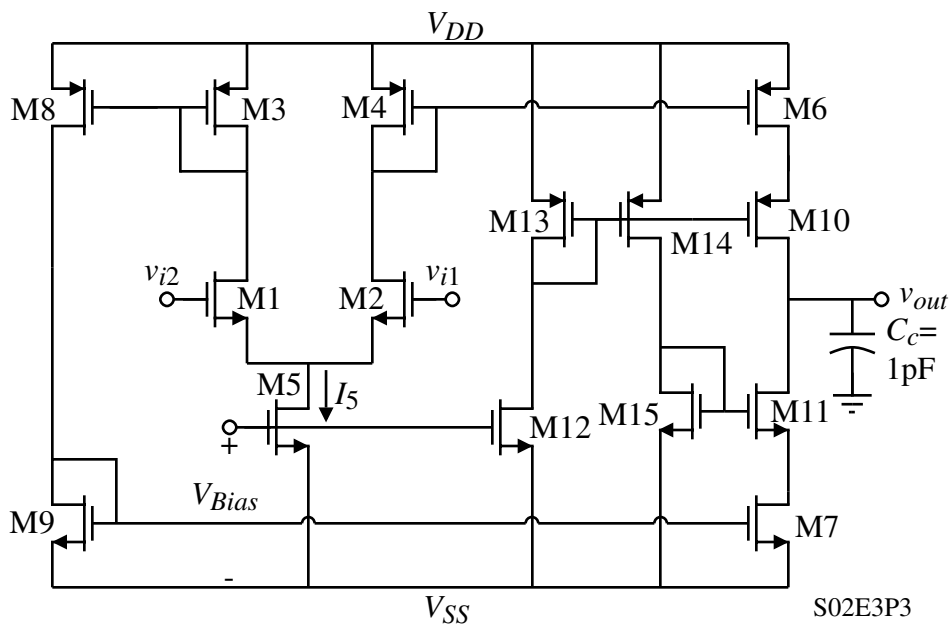


**Problem 3 - (25 points)**

Calculate the small-signal voltage gain, the  $SR$  ( $C_L = 1\text{pF}$ ), and the  $P_{diss}$  for the op amp shown where  $I_5 = 100\text{nA}$  and all transistors M1-M11 have a  $W/L$  of  $10\mu\text{m}/1\mu\text{m}$  and  $V_{DD} = -V_{SS} = 1.5\text{V}$ . If the minimum voltage across the drain-source of M6 and M7 are to be  $0.1\text{V}$ , design the  $W/L$  ratios of M12-M15 that give the maximum plus and minus output voltage swing assuming that transistors M12 and M15 have a current of  $50\text{nA}$ . The transistors are working in weak inversion and are modeled by the large signal model of

$$i_D = \frac{W}{L} I_{D0} \exp\left(\frac{v_{GS}}{nV_t}\right)$$

where  $I_{D0} = 2\text{nA}$  for PMOS and NMOS and  $n_P = 2.5$  and  $n_N = 1.5$ . Assume  $V_t = 26\text{mV}$  and  $\lambda_N = 0.4\text{V}^{-1}$  and  $\lambda_P = 0.5\text{V}^{-1}$ .

**Solution**

The small-signal voltage gain,  $A_v$ , is  $g_{m1}R_{out}$  (see end of solution) where,

$$R_{out} = (r_{ds6}g_{m10}r_{ds10}) \parallel (r_{ds7}g_{m11}r_{ds11})$$

With the currents and  $W/L$  ratios of transistors M1 through M11 known, we get

$$g_{m1} = g_{m11} = \frac{50\text{nA}}{1.5 \cdot 26\text{mV}} = 1.282\mu\text{S} \quad \text{and} \quad r_{ds7} = r_{ds11} = \frac{10^9}{0.04 \cdot 50} = 0.5 \times 10^9 \Omega$$

$$g_{m10} = \frac{50\text{nA}}{2.5 \cdot 26\text{mV}} = 0.769\mu\text{S} \quad \text{and} \quad r_{ds6} = r_{ds10} = \frac{10^9}{0.05 \cdot 50} = 0.4 \times 10^9 \Omega$$

$$R_{out} = (0.4 \times 10^9 \cdot 1.282 \times 10^{-6} \cdot 0.4 \times 10^9) \parallel (0.5 \times 10^9 \cdot 0.769 \times 10^{-6} \cdot 0.5 \times 10^9) = 9.924 \times 10^{10} \Omega$$

$$\therefore A_v = 1.282 \times 10^{-6} \cdot 9.924 \times 10^{10} = \underline{\underline{127,726 \text{ V/V}}}$$

$$SR = \frac{100\text{nA}}{1\text{pF}} = \underline{\underline{0.1\text{V}/\mu\text{s}}}$$

$$P_{diss} = 3\text{V}(50\text{nA} \cdot 6) = \underline{\underline{0.9\mu\text{W}}}$$

Problem 3 - Continued

Design of the  $W/L$ 's of M12 through M15:

To get 50nA in M12 means the  $W_{12}/L_{12} = 0.5(W_5/L_5) = \underline{5\mu\text{m}/1\mu\text{m}}$

M15:

$$V_{GS11} = n_N V_t \ln\left(\frac{I_D}{I_{DO}(W/L)}\right) = 1.5 \cdot 0.026 \ln\left(\frac{50}{2 \cdot 10}\right) = 0.0357\text{V}$$

$$\therefore V_{GS15} = 0.1 + 0.0357 = 0.1357\text{V} \rightarrow \frac{W_{15}}{L_{15}} = \frac{50\text{nA}}{2\text{nA} \cdot \exp\left(\frac{135.7}{1.5 \cdot 26}\right)} = \underline{0.77\mu\text{m}/1\mu\text{m}}$$

M13 and M14:

$$V_{SG10} = n_P V_t \ln\left(\frac{I_D}{I_{DO}(W/L)}\right) = 2.5 \cdot 0.026 \ln\left(\frac{50}{2 \cdot 10}\right) = 0.0596\text{V}$$

$$\therefore V_{GS13} = 0.1 + 0.0596 = 0.1596\text{V} \rightarrow \frac{W_{13}}{L_{13}} = \frac{50\text{nA}}{2\text{nA} \cdot \exp\left(\frac{159.6}{1.5 \cdot 26}\right)} = 2.146\mu\text{m}/1\mu\text{m}$$

Thus

$$\frac{W_{13}}{L_{13}} = \frac{W_{14}}{L_{14}} = \underline{2.146\mu\text{m}/1\mu\text{m}}$$

Comments on the small-signal gain:

It is much easier to use the expression  $g_{m1}R_{out}$  for the small-signal voltage gain. However, some prefer the following expression,

$$v_{out} = \left( \frac{g_{m1} \cdot g_{m8} \cdot g_{m7}}{2g_{m3} \cdot g_{m9}} + \frac{g_{m2} \cdot g_{m6}}{2g_{m4}} \right) R_{out}$$

which is equivalent since  $g_{m3}=g_{m8}$ ,  $g_{m7}=g_{m9}$ ,  $g_{m4}=g_{m6}$ , and  $g_{m1}=g_{m2}$ .